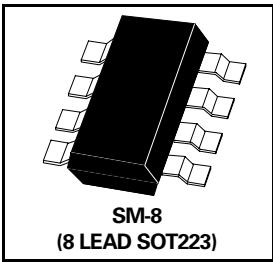
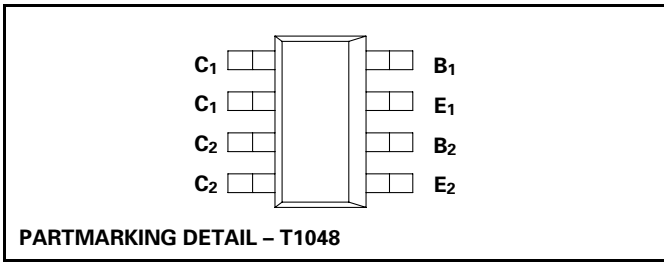


# SM-8 DUAL NPN MEDIUM POWER HIGH GAIN TRANSISTORS

ISSUE 2 - FEBRUARY 1996

## ZDT1048



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	17.5	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Peak Pulse Current	$I_{CM}$	20	A
Continuous Collector Current	$I_C$	5	A
Base Current	$I_B$	500	mA
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	°C

### THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^\circ\text{C}^*$ Any single die "on" Both die "on" equally	$P_{tot}$	2.25 2.75	W W
Derate above $25^\circ\text{C}^*$ Any single die "on" Both die "on" equally		18 22	mW/°C mW/°C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		55.6 45.5	°C/W °C/W

\* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

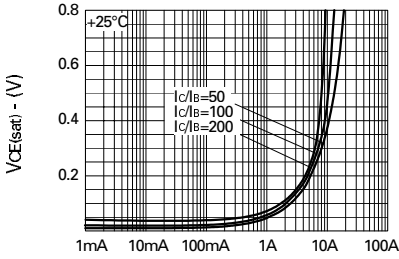
# ZDT1048

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

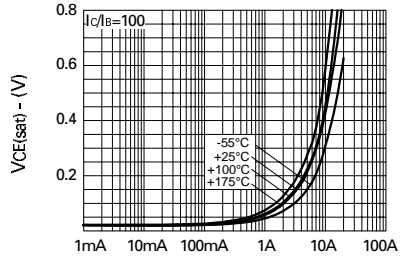
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50	85		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{CES}$	50	85		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{CEO}$	17.5	24		V	$I_C=10\text{mA}$
Collector-Emitter Breakdown Voltage	$V_{CEV}$	50	85		V	$I_C=100\mu\text{A}, V_{EB}=1\text{V}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	8.7		V	$I_E=100\mu\text{A}$
Collector Cutoff Current	$I_{CBO}$		0.3	10	nA	$V_{CB}=35\text{V}$
Emitter Cutoff Current	$I_{EBO}$		0.3	10	nA	$V_{EB}=4\text{V}$
Collector Emitter Cutoff Current	$I_{CES}$		0.3	10	nA	$V_{CES}=35\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		27 55 120 200 200	45 75 160 240 300	mV mV mV mV mV	$I_C=0.5\text{A}, I_B=10\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$ $I_C=2\text{A}, I_B=10\text{mA}^*$ $I_C=5\text{A}, I_B=100\text{mA}^*$ $I_C=5\text{A}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1000	1100	mV	$I_C=5\text{A}, I_B=100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		900	1000	mV	$I_C=5\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	280 300 300 250 50	440 450 450 300 80	1200		$I_C=10\text{mA}, V_{CE}=2\text{V}^*$ $I_C=0.5\text{A}, V_{CE}=2\text{V}^*$ $I_C=1\text{A}, V_{CE}=2\text{V}^*$ $I_C=5\text{A}, V_{CE}=2\text{V}^*$ $I_C=20\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	$f_T$		150		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=50\text{MHz}$
Output Capacitance	$C_{obo}$		60	80	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	$t_{on}$		120		ns	$I_C=4\text{A}, I_B=40\text{mA}, V_{CC}=10\text{V}$
	$t_{off}$		250		ns	$I_C=4\text{A}, I_B=\pm 40\text{mA}, V_{CC}=10\text{V}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

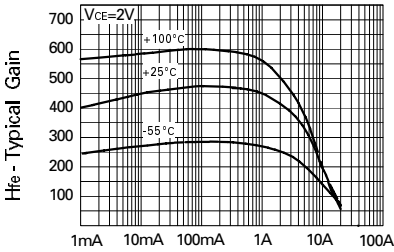
## TYPICAL CHARACTERISTICS



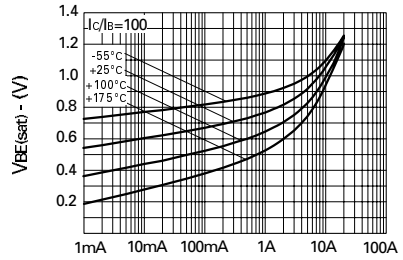
$V_{CE(sat)}$  v  $I_C$



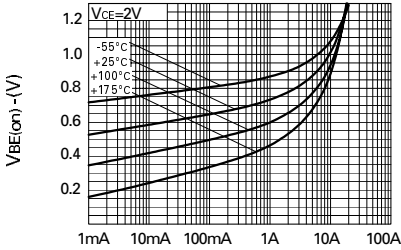
$V_{CE(sat)}$  v  $I_C$



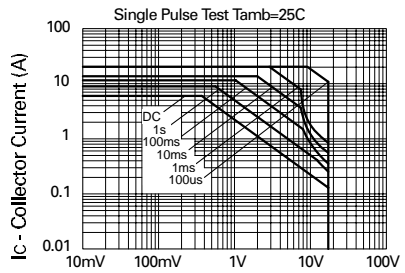
$H_{fe}$  v  $I_C$



$V_{BE(sat)}$  v  $I_C$



$V_{BE(on)}$  v  $I_C$



$V_{CE}$  - Collector Voltage  
Safe Operating Area